

INCHANGE Semiconductor

isc Product Specification

isc Silicon NPN Power Transistor

2SC2414

DESCRIPTION

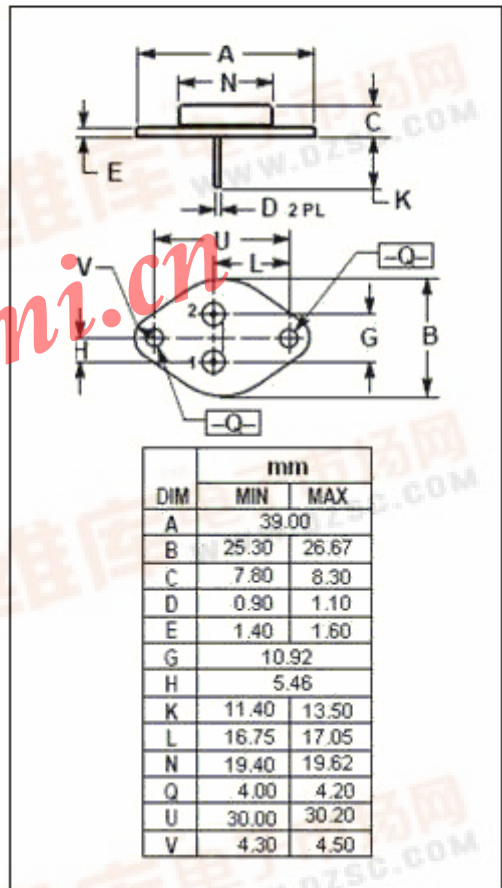
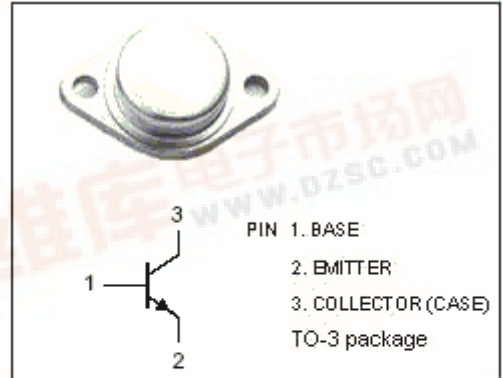
- High Switching Speed
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 400V$ (Min)

APPLICATIONS

- Designed for high speed power switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	2	A
I_{CM}	Collector Current-Peak	4	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	70	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.2A; L=25mH$	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1A; I_B=0.2A$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=1A; I_B=0.2A$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=500V; I_E=0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5V; I_C=0$			0.1	mA
h_{FE-1}	DC Current Gain	$I_C=0.1A; V_{CE}=5V$	15			
h_{FE-2}	DC Current Gain	$I_C=1A; V_{CE}=5V$	8			
f_T	Current-Gain—Bandwidth Product	$I_C=0.2A; V_{CE}=10V$		11		MHz

Switching Times , Resistive Load

t_{on}	Turn-On Time	$I_C=1A; I_{B1}=-I_{B2}=0.2A$			1	μs
t_{stg}	Storage Time				3	μs
t_f	Fall Time				1	μs